

**SOT-23 DIGITAL TRANSISTORS  
TRANSISTORS(PNP)**

**FEATURES**

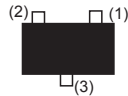
- \* Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.(see equivalent circuit).
- \* The bias resistors consist of thin-film resistors with complete isolation to without connecting external input. They also have the advantage of almost completely eliminating parasitic effects.
- \* Only the on/off conditions need to be set for operation making device design easy.

**MECHANICAL DATA**

- \* Case: Molded plastic
- \* Epoxy: UL 94V-O rate flame retardant
- \* Lead: MIL-STD-202E method 208C guaranteed
- \* Mounting position: Any
- \* Weight: 0.008 gram

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified.



- (1) BASE
- (2) EMITTER
- (3) COLLECTOR

**MAXIMUM RATINGS** ( @ TA = 25°C unless otherwise noted )

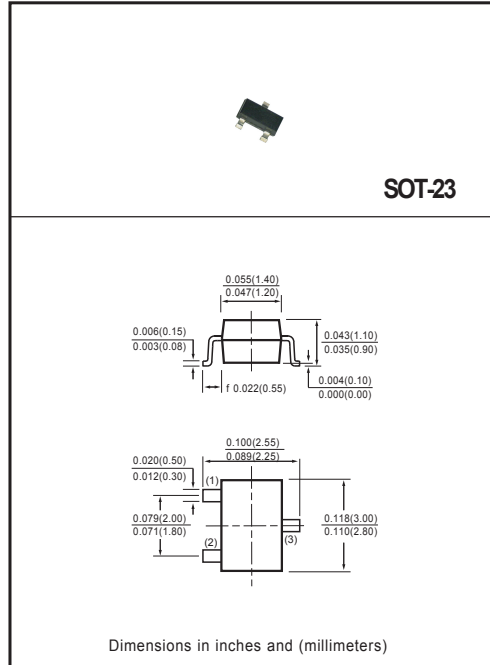
RATINGS	SYMBOL	VALUE	UNITS
Collector-Base Voltage	V <sub>CB0</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-50	V
Emitter-base Voltage	V <sub>EBO</sub>	-5	V
Collector Continuous Current	I <sub>C</sub>	-100	mA
Collector Dissipation	P <sub>C</sub>	200	mW
Junction and storage Temperature	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ELECTRICAL CHARACTERISTICS** ( @ TA = 25°C unless otherwise noted )

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Collector-base breakdown voltage (I <sub>C</sub> = -50μA, I <sub>E</sub> =0)	V <sub>(BR)CBO</sub>	-50	-	-	V
Collector-emitter breakdown voltage (I <sub>C</sub> = -1mA, I <sub>B</sub> =0)	V <sub>(BR)CEO</sub>	-50	-	-	V
Emitter-base breakdown voltage (I <sub>E</sub> = -50μA, I <sub>C</sub> =0)	V <sub>(BR)EBO</sub>	-5	-	-	V
Collector cut-off current (V <sub>CB</sub> = -50V, I <sub>E</sub> =0)	I <sub>CBO</sub>	-	-	-0.5	μA
Emitter cut-off current (V <sub>EB</sub> = -4V, I <sub>C</sub> =0)	I <sub>EBO</sub>	-	-	-0.5	μA
DC current gain (V <sub>CE</sub> = -5V, I <sub>C</sub> = -1mA)	h <sub>FE</sub>	100	250	600	
Collector-emitter saturation voltage (I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA)	V <sub>CE(sat)</sub>	-	-	-0.3	V
Transistion frequency (V <sub>CE</sub> = -10V, I <sub>C</sub> = -5mA, f=100MHz)	f <sub>T</sub>	-	250	-	MHz
Input resistor	R <sub>1</sub>	7	10	13	KΩ

Note: "Fully ROHS compliant", "100% Sn plating (Pb-free)".

2006-3



## RATING AND CHARACTERISTICS CURVES ( DTA114TCA )

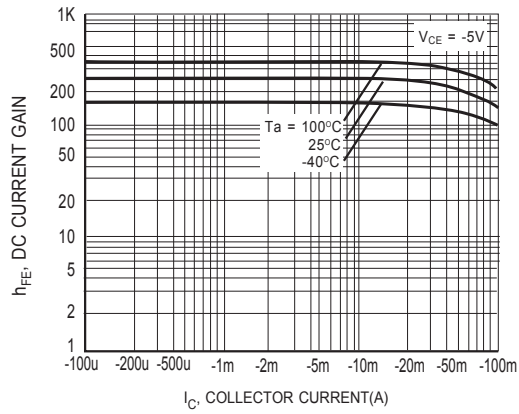


Figure 1 DC current gain vs. collector current

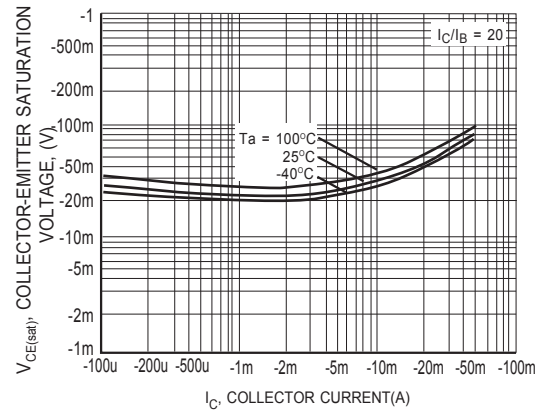


Figure 2 Collector-emitter saturation voltage vs. collector current

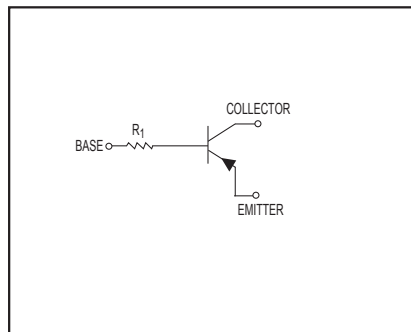


Figure3 Equivalent circuit

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